1. General description

The 74LVC2G241 is a dual non-inverting buffer/line driver with 3-state outputs. The 3-state outputs are controlled by the output enable inputs $1\overline{OE}$ and 2OE:

- A HIGH level at pin 10E causes output 1Y to assume a high-impedance OFF-state.
- A LOW level at pin 2OE causes output 2Y to assume a high-impedance OFF-state.

Schmitt trigger action at all inputs makes the circuit highly tolerant of slower input rise and fall times.

Inputs can be driven from either 3.3 V or 5 V devices. This feature allows the use of the 74LVC2G241 as a translator in a mixed 3.3 V and 5 V environment.

This device is fully specified for partial power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing a damaging backflow current through the device when it is powered down.

2. Features and benefits

- Wide supply voltage range from 1.65 V to 5.5 V
- 5 V tolerant input/output for interfacing with 5 V logic
- High noise immunity
- Complies with JEDEC standard:
 - ◆ JESD8-7 (1.65 V to 1.95 V)
 - ◆ JESD8-5 (2.3 V to 2.7 V)
 - JESD8-B/JESD36 (2.7 V to 3.6 V)
- ESD protection:
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V
- ± 24 mA output drive (V_{CC} = 3.0 V)
- CMOS low power consumption
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels
- Inputs accept voltages up to 5 V
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C





3. Ordering information

Table 1. Ordering	g information							
Type number	Package							
	Temperature range Name		Description	Version				
74LVC2G241DP	–40 °C to +125 °C	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm	SOT505-2				
74LVC2G241DC	–40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1				
74LVC2G241GT	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 1 \times 1.95 \times 0.5 mm	SOT833-1				
74LVC2G241GF	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body $1.35 \times 1 \times 0.5$ mm	SOT1089				
74LVC2G241GD	–40 °C to +125 °C	XSON8U	plastic extremely thin small outline package; no leads; 8 terminals; UTLP based; body $3 \times 2 \times 0.5$ mm	SOT996-2				
74LVC2G241GM	–40 °C to +125 °C	XQFN8U	plastic extremely thin quad flat package; no leads; 8 terminals; UTLP based; body $1.6 \times 1.6 \times 0.5$ mm	SOT902-1				
74LVC2G241GN	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body $1.2 \times 1.0 \times 0.35$ mm	SOT1116				
74LVC2G241GS	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.35 \times 1.0 \times 0.35 mm	SOT1203				

4. Marking

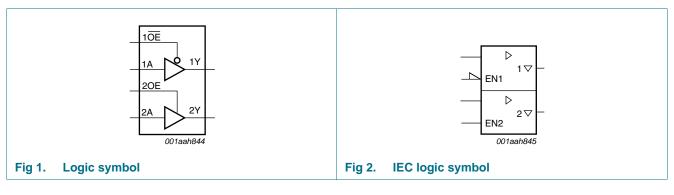
Table 2.Marking codes

Type number	Marking code ^[1]
74LVC2G241DP	V241
74LVC2G241DC	V41
74LVC2G241GT	V41
74LVC2G241GF	V1
74LVC2G241GD	V41
74LVC2G241GM	V41
74LVC2G241GN	V1
74LVC2G241GS	V1

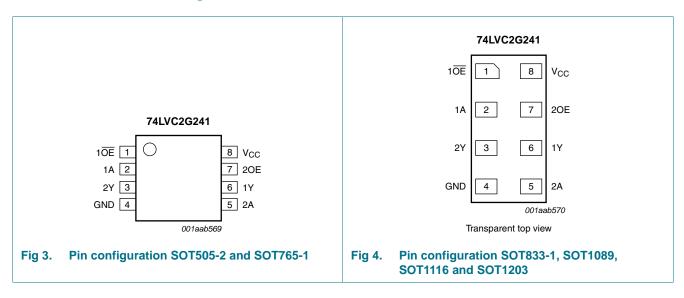
[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

Dual buffer/line driver; 3-state

5. Functional diagram

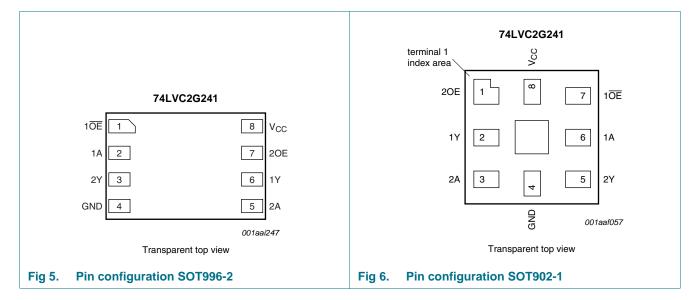


Pinning information 6.



6.1 Pinning





6.2 Pin description

Symbol	Pin		Description	
	SOT505-2, SOT765-1, SOT833-1, SOT1089, SOT996-2, SOT1116 and SOT1203	SOT902-1		
1 <mark>OE</mark>	1	7	output enable input (active LOW)	
1A, 2A	2, 5	6, 3	data input	
GND	4	4	ground (0 V)	
1Y, 2Y	6, 3	2, 5	data output	
2OE	7	1	output enable input (active HIGH)	
V _{CC}	8	8	supply voltage	

7. Functional description

Table 4.Function table^[1]

Input				Output		
1 <mark>0E</mark>	1A	20E	2A	1Y	2Y	
L	L	Н	L	L	L	
L	Н	Н	Н	Н	Н	
Н	Х	L	Х	Z	Z	

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

				10	,
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+6.5	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
VI	input voltage		<u>[1]</u> –0.5	+6.5	V
I _{OK}	output clamping current	$V_{\rm O}$ > $V_{\rm CC}$ or $V_{\rm O}$ < 0 V	-	±50	mA
Vo	output voltage	enable mode	<u>[1]</u> –0.5	$V_{CC} + 0.5$	V
		disable mode	<u>[1]</u> –0.5	+6.5	V
		Power-down mode	<u>[1][2]</u> –0.5	+6.5	V
lo	output current	$V_{O} = 0 V$ to V_{CC}	-	±50	mA
I _{CC}	supply current		-	100	mA
I _{GND}	ground current		-100	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 \ ^{\circ}C \ to +125 \ ^{\circ}C$	[3] _	300	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] When $V_{CC} = 0$ V (Power-down mode), the output voltage can be 5.5 V in normal operation.

[3] For TSSOP8 packages: above 55 °C the value of P_{tot} derates linearly at 2.5 mW/K.
 For VSSOP8 packages: above 110 °C the value of P_{tot} derates linearly at 8.0 mW/K.
 For XSON8, XSON8U and XQFN8U packages: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

9. Recommended operating conditions

Table 6.	Operating conditions				
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		1.65	5.5	V
VI	input voltage		0	5.5	V
Vo	output voltage	V_{CC} = 1.65 V to 5.5 V; enable mode	0	V _{CC}	V
		V_{CC} = 1.65 V to 5.5 V; disable mode	0	5.5	V
		V _{CC} = 0 V; Power-down mode	0	5.5	V
T _{amb}	ambient temperature		-40	+125	°C
$\Delta t / \Delta V$	input transition rise and fall rate	V_{CC} = 1.65 V to 2.7 V	-	20	ns/V
		$V_{CC} = 2.7 \text{ V to } 5.5 \text{ V}$	-	10	ns/V

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ <mark>[1]</mark>	Max	Unit
T _{amb} = -	40 °C to +85 °C					
V _{IH}	HIGH-level input voltage	V _{CC} = 1.65 V to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		V_{CC} = 2.3 V to 2.7 V	1.7	-	-	V
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	2.0	-	-	V
		V_{CC} = 4.5 V to 5.5 V	$0.7\times V_{CC}$	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 1.65 V to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	-	-	0.8	V
		V_{CC} = 4.5 V to 5.5 V	-	-	$0.3\times V_{CC}$	V
V _{OL}	LOW-level output voltage	$V_I = V_{IH} \text{ or } V_{IL}$				
		I_{O} = 100 $\mu A;$ V_{CC} = 1.65 V to 5.5 V	-	-	0.1	V
		$I_0 = 4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.45	V
		$I_0 = 8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.3	V
		$I_0 = 12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	-	-	0.4	V
		$I_0 = 24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.55	V
		$I_0 = 32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.55	V
V _{OH}	HIGH-level output voltage	$V_I = V_{IH} \text{ or } V_{IL}$				
		I_{O} = –100 $\mu\text{A};$ V_{CC} = 1.65 V to 5.5 V	$V_{CC}-0.1$	-	-	V
		$I_0 = -4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.2	-	-	V
		$I_0 = -8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.9	-	-	V
		$I_0 = -12 \text{ mA}; \text{ V}_{CC} = 2.7 \text{ V}$	2.2	-	-	V
		$I_0 = -24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.3	-	-	V
		$I_O = -32$ mA; $V_{CC} = 4.5$ V	3.8	-	-	V
lı	input leakage current	$V_{\rm I}$ = 5.5 V or GND; V_{CC} = 0 V to 5.5 V	-	±0.1	±5	μΑ
I _{OZ}	OFF-state output current	$ V_{I} = V_{IH} \text{ or } V_{IL}; V_{O} = 5.5 \text{ V or GND}; $	-	±0.1	±10	μA
I _{OFF}	power-off leakage current	V_{I} or V_{O} = 5.5 V; V_{CC} = 0 V	-	±0.1	±10	μA
I _{CC}	supply current	$V_{I} = 5.5 \text{ V or GND}; I_{O} = 0 \text{ A};$ $V_{CC} = 1.65 \text{ V to } 5.5 \text{ V}$	-	0.1	10	μΑ
Δl _{CC}	additional supply current	per pin; V _I = V _{CC} – 0.6 V; I _O = 0 A; V _{CC} = 2.3 V to 5.5 V	-	5	500	μΑ
CI	input capacitance		-	2	-	pF

Dual buffer/line driver; 3-state

Symbol	Parameter	Conditions	Min	Typ <mark>[1]</mark>	Max	Unit
T _{amb} = -	40 °C to +125 °C					
V _{IH}	HIGH-level input voltage	V _{CC} = 1.65 V to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		V_{CC} = 2.3 V to 2.7 V	1.7	-	-	V
		$V_{CC} = 2.7 V \text{ to } 3.6 V$	2.0	-	-	V
		V_{CC} = 4.5 V to 5.5 V	$0.7\times V_{CC}$	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 1.65 V to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		$V_{CC} = 2.7 V \text{ to } 3.6 V$	-	-	0.8	V
		$V_{CC} = 4.5 V \text{ to } 5.5 V$	-	-	$0.3 \times V_{\text{CC}}$	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_{O} = 100 μ A; V_{CC} = 1.65 V to 5.5 V	-	-	0.1	V
		$I_{O} = 4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.70	V
		$I_{O} = 8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.45	V
		$I_0 = 12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	-	-	0.60	V
		$I_0 = 24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.80	V
		$I_{O} = 32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.80	V
V _{он}	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_{O} = –100 $\mu A;$ V_{CC} = 1.65 V to 5.5 V	$V_{CC}-0.1$	-	-	V
		$I_0 = -4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	0.95	-	-	V
		$I_{O} = -8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.7	-	-	V
		$I_{O} = -12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	1.9	-	-	V
		$I_{O} = -24$ mA; $V_{CC} = 3.0$ V	2.0	-	-	V
		$I_{O} = -32$ mA; $V_{CC} = 4.5$ V	3.4	-	-	V
l _l	input leakage current	V_{I} = 5.5 V or GND; V_{CC} = 0 V to 5.5 V	-	-	±20	μA
OZ	OFF-state output current	$V_{I} = V_{IH} \text{ or } V_{IL}; V_{O} = 5.5 \text{ V or GND};$ $V_{CC} = 3.6 \text{ V}$	-	-	±20	μA
OFF	power-off leakage current	V_{I} or V_{O} = 5.5 V; V_{CC} = 0 V	-	-	±20	μΑ
lcc	supply current	$V_{I} = 5.5 V \text{ or GND}; I_{O} = 0 A;$ $V_{CC} = 1.65 V \text{ to } 5.5 V$	-	-	40	μΑ
∆l _{CC}	additional supply current	per pin; V _I = V _{CC} – 0.6 V; I _O = 0 A; V _{CC} = 2.3 V to 5.5 V	-	-	5	mA

Table 7. Static characteristics ...continued

[1] Typical values are measured at V_{CC} = 3.3 V and T_{amb} = 25 °C.

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see <u>Figure 10</u>.

Symbol	Parameter	Conditions			0 °C to +85 °	°C	–40 °C to +125 °C		
			-	Min	Typ <mark>[1]</mark>	Max	Min	Max	
t _{pd}	propagation delay	nA to nY; see Figure 7	[2]						
		V_{CC} = 1.65 V to 1.95 V		1.0	4.5	8.8	1.0	11.0	ns
		V_{CC} = 2.3 V to 2.7 V		0.5	2.8	4.9	0.5	6.3	ns
		$V_{CC} = 2.7 V$		1.0	2.8	4.7	1.0	5.9	ns
		V_{CC} = 3.0 V to 3.6 V		0.5	2.6	4.3	0.5	5.4	ns
		V_{CC} = 4.5 V to 5.5 V		0.5	2.1	3.7	0.5	4.6	ns
t _{en}	enable time	1OE to 1Y; see Figure 8	<u>[3]</u>						
		V_{CC} = 1.65 V to 1.95 V		1.5	5.2	9.9	1.5	12.4	ns
		V_{CC} = 2.3 V to 2.7 V		1.0	3.1	5.6	1.0	7.0	ns
		$V_{CC} = 2.7 V$		1.5	3.2	5.5	1.5	6.9	ns
		V_{CC} = 3.0 V to 3.6 V		0.5	2.7	4.7	0.5	5.9	ns
		V_{CC} = 4.5 V to 5.5 V		0.5	2.0	3.8	0.5	4.8	ns
		2OE to 2Y; see Figure 9	<u>[3]</u>						
		V_{CC} = 1.65 V to 1.95 V		1.0	4.3	8.8	1.0	11.0	ns
		V_{CC} = 2.3 V to 2.7 V		1.0	2.7	4.7	1.0	5.9	ns
		$V_{CC} = 2.7 V$		1.0	2.7	4.6	1.0	5.8	ns
		V_{CC} = 3.0 V to 3.6 V		1.0	2.5	4.1	1.0	5.1	ns
		V_{CC} = 4.5 V to 5.5 V		0.5	1.9	3.3	0.5	4.1	ns
t _{dis}	disable time	1OE to 1Y; see Figure 8	[4]						
		V_{CC} = 1.65 V to 1.95 V		1.0	3.2	11.6	1.0	14.1	ns
		V_{CC} = 2.3 V to 2.7 V		0.5	2.2	5.8	0.5	7.6	ns
		$V_{CC} = 2.7 V$		1.0	2.8	4.6	1.0	5.9	ns
		V_{CC} = 3.0 V to 3.6 V		1.0	2.6	4.4	1.0	5.7	ns
		V_{CC} = 4.5 V to 5.5 V		0.5	2.0	3.4	0.5	4.6	ns
		2OE to 2Y; see Figure 9	<u>[4]</u>						
		V_{CC} = 1.65 V to 1.95 V		1.0	3.6	12.5	1.0	15.2	ns
		V_{CC} = 2.3 V to 2.7 V		0.5	2.0	5.2	0.5	6.9	ns
		$V_{CC} = 2.7 V$		1.5	3.2	4.9	1.5	6.3	ns
		V_{CC} = 3.0 V to 3.6 V		1.0	2.8	4.2	1.0	5.4	ns
		$V_{CC} = 4.5 \text{ V} \text{ to } 5.5 \text{ V}$		0.5	2.0	3.3	0.5	4.4	ns

Symbol	Parameter	Conditions		−40 °C to +85 °C			–40 °C to +125 °C	
			Min	Typ <mark>[1]</mark>	Max	Min	Max	1
C _{PD} power dissipation capacitance	per buffer; $V_I = GND$ to V_{CC}	[5]						
	capacitance	output enabled	-	20	-	-	-	pF
		output disabled	-	5	-	-	-	pF

Table 8. Dynamic characteristics ... continued

-----0 1 A C

[1] Typical values are measured at nominal V_{CC} and at $T_{amb} = 25$ °C.

[2] t_{pd} is the same as t_{PLH} and t_{PHL} .

[3] t_{en} is the same as t_{PZH} and t_{PZL} .

[4] t_{dis} is the same as t_{PLZ} and t_{PHZ} .

[5] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W).

 $P_{D} = C_{PD} \times V_{CC}^{2} \times f_{i} \times N + \Sigma (C_{L} \times V_{CC}^{2} \times f_{o}) \text{ where:}$

 f_i = input frequency in MHz;

 $f_o = output frequency in MHz;$

 C_L = output load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o) = \text{sum of outputs.}$

12. Waveforms

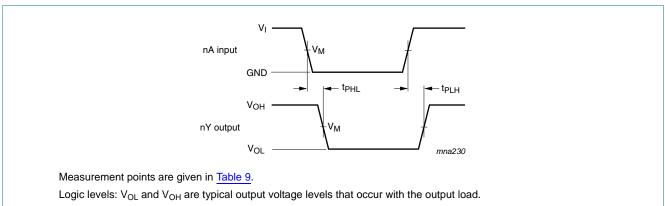


Fig 7. The data input (nA) to output (nY) propagation delays

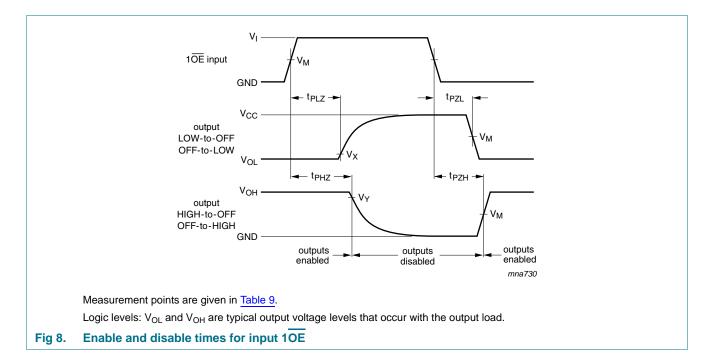
Table 9. **Measurement points**

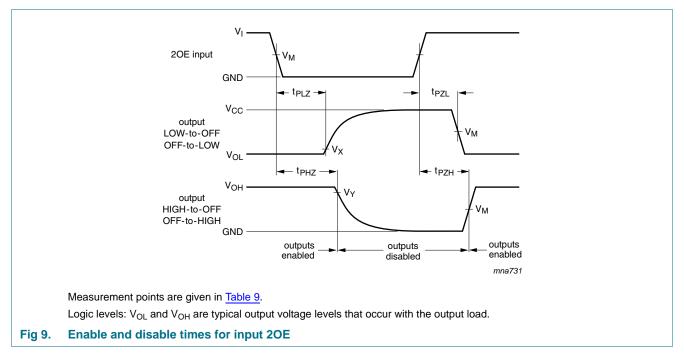
Supply voltage	Input	Output		
V _{cc}	V _M	V _M	V _X	V _Y
1.65 V to 1.95 V	$0.5\times V_{CC}$	$0.5\times V_{\text{CC}}$	V _{OL} + 0.15 V	$V_{OH} - 0.15 \ V$
2.3 V to 2.7 V	$0.5\times V_{CC}$	$0.5\times V_{CC}$	V _{OL} + 0.15 V	V _{OH} – 0.15 V
2.7 V	1.5 V	1.5 V	V _{OL} + 0.3 V	$V_{OH} - 0.3 \ V$
3.0 V to 3.6 V	1.5 V	1.5 V	V _{OL} + 0.3 V	$V_{OH} - 0.3 \ V$
4.5 V to 5.5 V	$0.5\times V_{CC}$	$0.5\times V_{CC}$	V _{OL} + 0.3 V	$V_{OH} - 0.3 V$

NXP Semiconductors

74LVC2G241

Dual buffer/line driver; 3-state

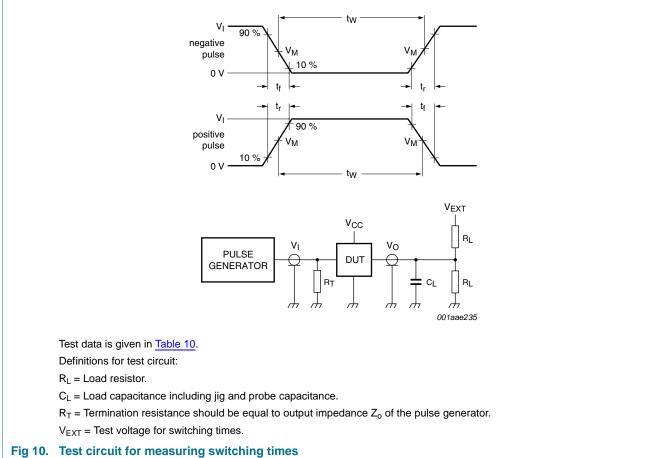




NXP Semiconductors

74LVC2G241

Dual buffer/line driver; 3-state



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	Tabl	e 1	0.	Test	data
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Supply voltage	Input	Load		V _{EXT}		
	VI	CL	RL	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}
1.65 V to 1.95 V	V _{CC}	30 pF	1 kΩ	open	GND	$2 \times V_{CC}$
2.3 V to 2.7 V	V _{CC}	30 pF	500 Ω	open	GND	$2 \times V_{CC}$
2.7 V	2.7 V	50 pF	500 Ω	open	GND	6 V
3.0 V to 3.6 V	2.7 V	50 pF	500 Ω	open	GND	6 V
4.5 V to 5.5 V	V _{CC}	50 pF	500 Ω	open	GND	$2 \times V_{CC}$

Dual buffer/line driver; 3-state

13. Package outline

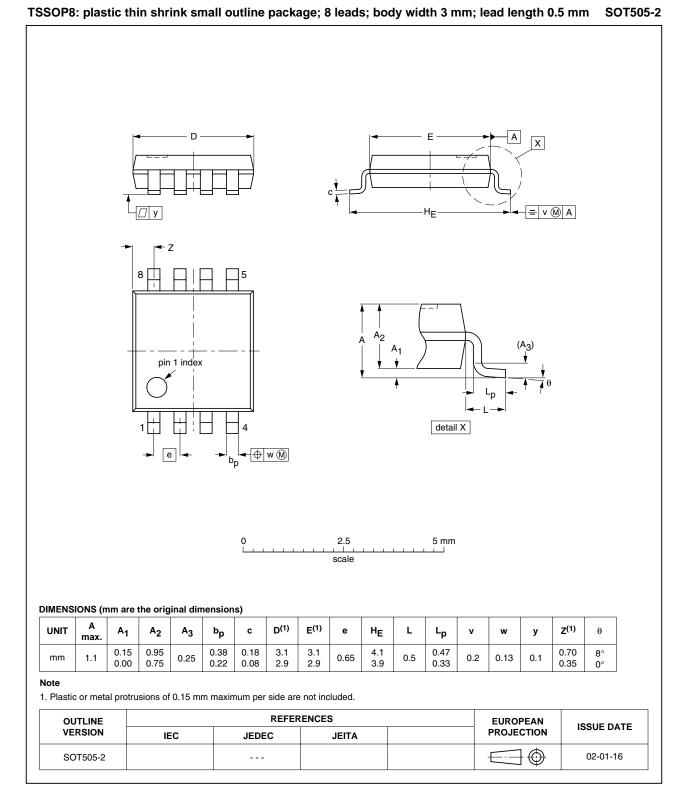


Fig 11. Package outline SOT505-2 (TSSOP8)

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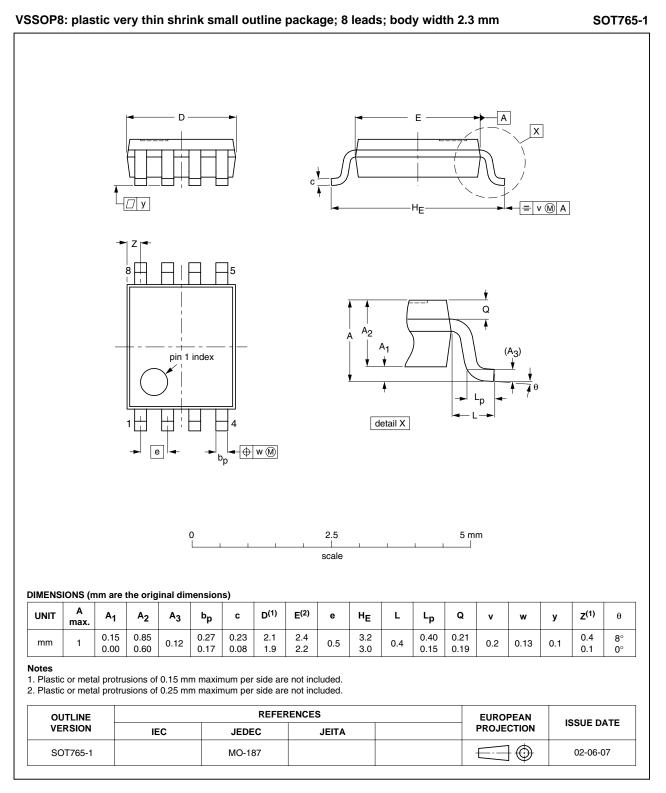


Fig 12. Package outline SOT765-1 (VSSOP8)

74LVC2G241 Product data sheet

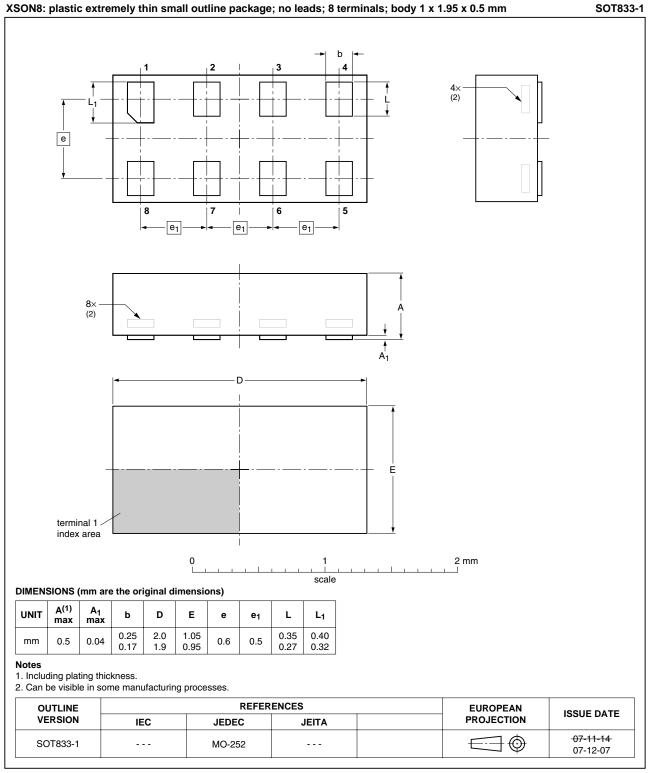
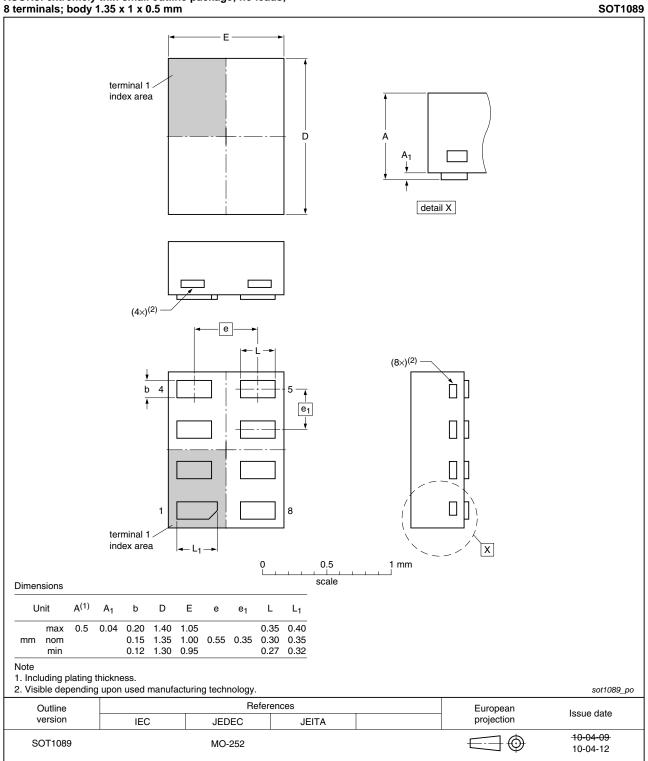


Fig 13. Package outline SOT833-1 (XSON8)

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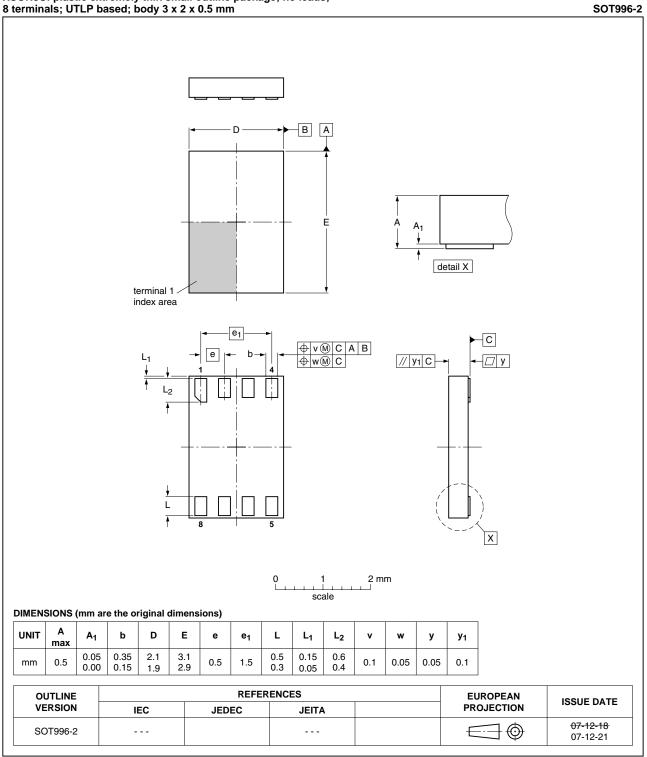


XSON8: extremely thin small outline package; no leads; 8 terminals; body 1.35 x 1 x 0.5 mm

Fig 14. Package outline SOT1089 (XSON8)

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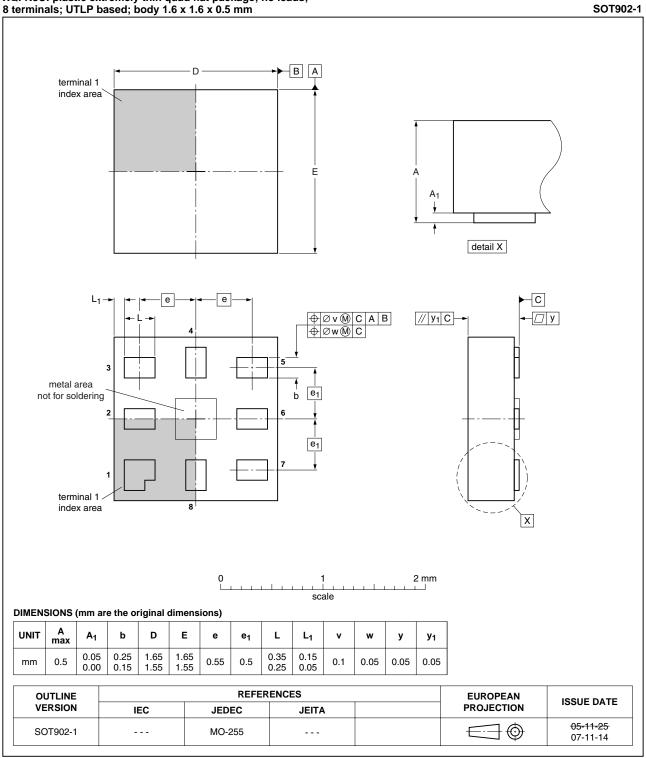




XSON8U: plastic extremely thin small outline package; no leads; 8 terminals; UTLP based; body 3 x 2 x 0.5 mm

Fig 15. Package outline SOT996-2 (XSON8U)

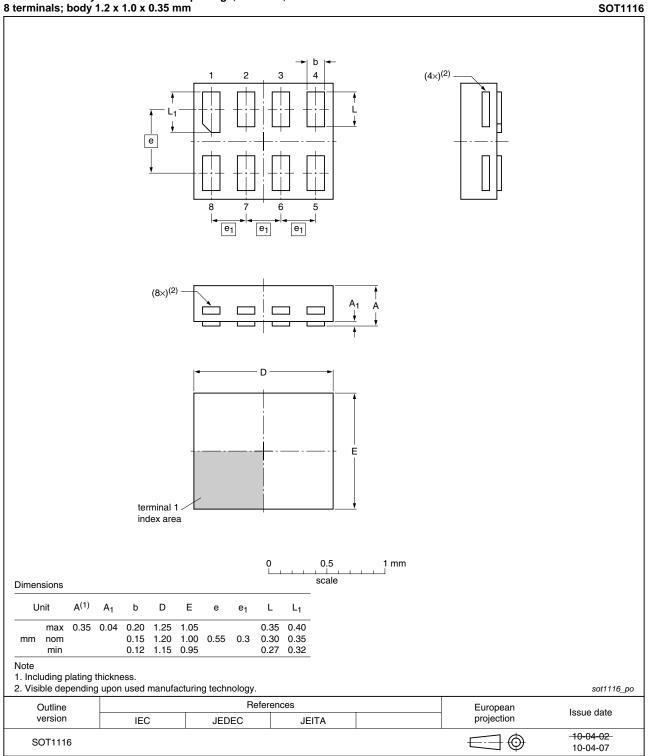




XQFN8U: plastic extremely thin quad flat package; no leads; 8 terminals; UTLP based; body 1.6 x 1.6 x 0.5 mm

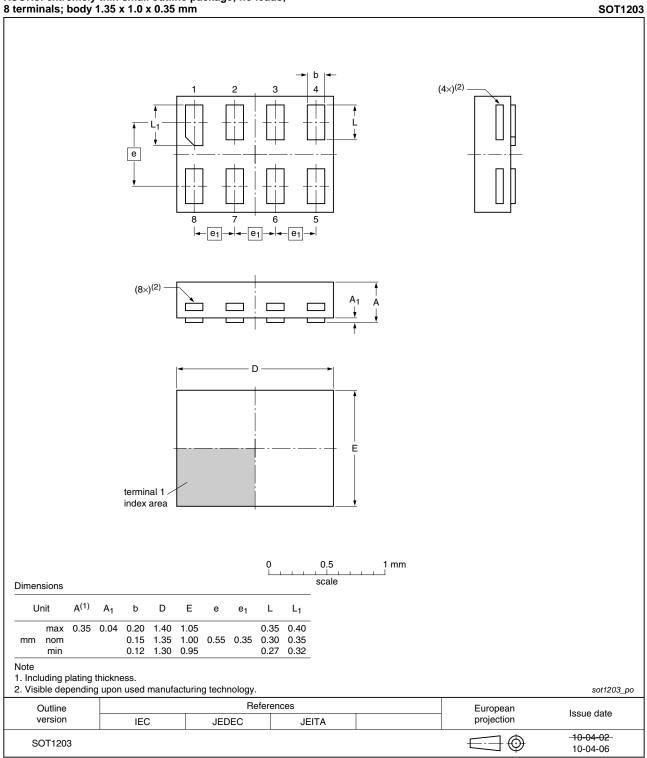
Fig 16. Package outline SOT902-1 (XQFN8U)

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XSON8: extremely thin small outline package; no leads; 8 terminals; body 1.2 x 1.0 x 0.35 mm

Fig 17. Package outline SOT1116 (XSON8)



XSON8: extremely thin small outline package; no leads; 8 terminals; body 1.35 x 1.0 x 0.35 mm

Fig 18. Package outline SOT1203 (XSON8)



14. Abbreviations

Table 11. Abbreviations		
Acronym	Description	
CMOS	Complementary Metal-Oxide Semiconductor	
DUT	Device Under Test	
ESD	ElectroStatic Discharge	
HBM	Human Body Model	
MM	Machine Model	
TTL	Transistor-Transistor Logic	

15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVC2G241 v.10	20100806	Product data sheet	-	74LVC2G241 v.9
Modifications:	 Figure 5: on 	pin 7, $2\overline{OE}$ changed to $2OE$.		
	 Added type 	number 74LVC2G241GF (SO	T1089/XSON8 packa	ige).
	 Added type 	number 74LVC2G241GN (SO	T1116/XSON8 packa	ige).
	 Added type 	number 74LVC2G241GS (SO	T1203/XSON8 packa	age).
74LVC2G241 v.9	20080610	Product data sheet	-	74LVC2G241 v.8
74LVC2G241 v.8	20080312	Product data sheet	-	74LVC2G241 v.7
74LVC2G241 v.7	20071005	Product data sheet	-	74LVC2G241 v.6
74LVC2G241 v.6	20060922	Product data sheet	-	74LVC2G241 v.5
74LVC2G241 v.5	20050202	Product specification	-	74LVC2G241 v.4
74LVC2G241 v.4	20040922	Product specification	-	74LVC2G241 v.3
74LVC2G241 v.3	20030311	Product specification	-	74LVC2G241 v.2
74LVC2G241 v.2	20030129	Product specification	-	74LVC2G241 v.1
74LVC2G241 v.1	20021030	Product specification	-	-

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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Product data sheet

Dual buffer/line driver; 3-state

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Dual buffer/line driver; 3-state

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